

isc Silicon NPN Power Transistor

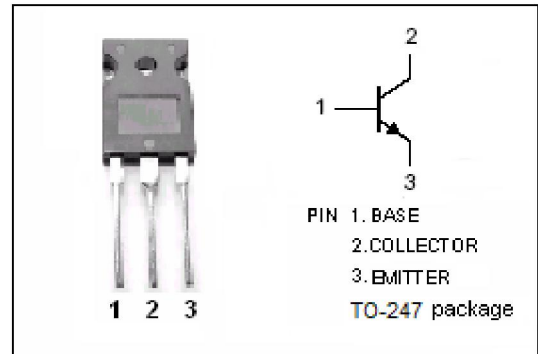
BU2527AW

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 800V(\text{Min})$
- High Switching Speed

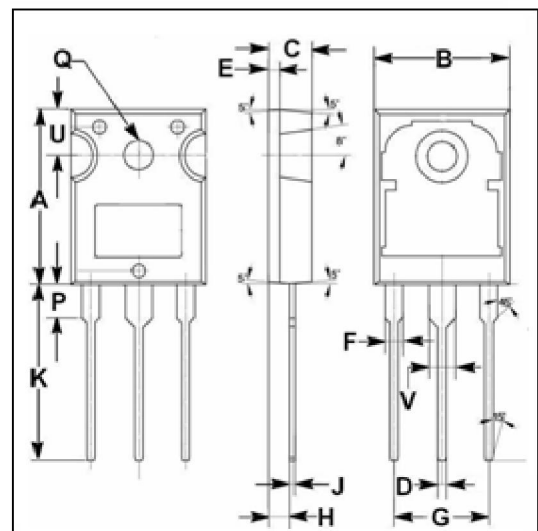
APPLICATIONS

- Designed for use in horizontal deflection circuits of high resolution monitors.



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector-Emitter Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	7.5	V
I_C	Collector Current-Continuous	12	A
I_{CM}	Collector Current-Peak	30	A
I_B	Base Current-Continuous	8	A
I_{BM}	Base Current-Peak	12	A
P_C	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	125	W
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$



DIM	mm	
	MIN	MAX
A	19.80	20.20
B	15.40	15.80
C	4.90	5.10
D	0.90	1.10
E	1.40	1.60
F	1.90	2.10
G	10.80	11.00
H	2.40	2.60
J	0.50	0.70
K	19.50	20.50
P	3.90	4.10
Q	3.30	3.50
U	5.20	5.40
V	2.90	3.10

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.0	$^\circ\text{C/W}$

isc Silicon NPN Power Transistor**BU2527AW****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 100mA; I _B = 0; L= 25mH	800			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA; I _C = 0	7.5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 6A ; I _B = 1.2A			5.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 6A ; I _B = 1.2A			1.3	V
I _{CES}	Collector Cutoff Current	V _{CE} =1500V, V _{BE} =0 V _{CE} =1500V, V _{BE} =0; T _C =125°C			0.25 2.0	mA
h _{FE-1}	DC Current Gain	I _C = 1A ; V _{CE} = 5V		10		
h _{FE-2}	DC Current Gain	I _C = 6A ; V _{CE} = 5V	5		9	
C _{OB}	Output Capacitance	I _E = 0 ; V _{CB} = 10V; f _{test} = 1MHz		145		pF